

# Schottky Barrier Rectifier

# SBL1060

### FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

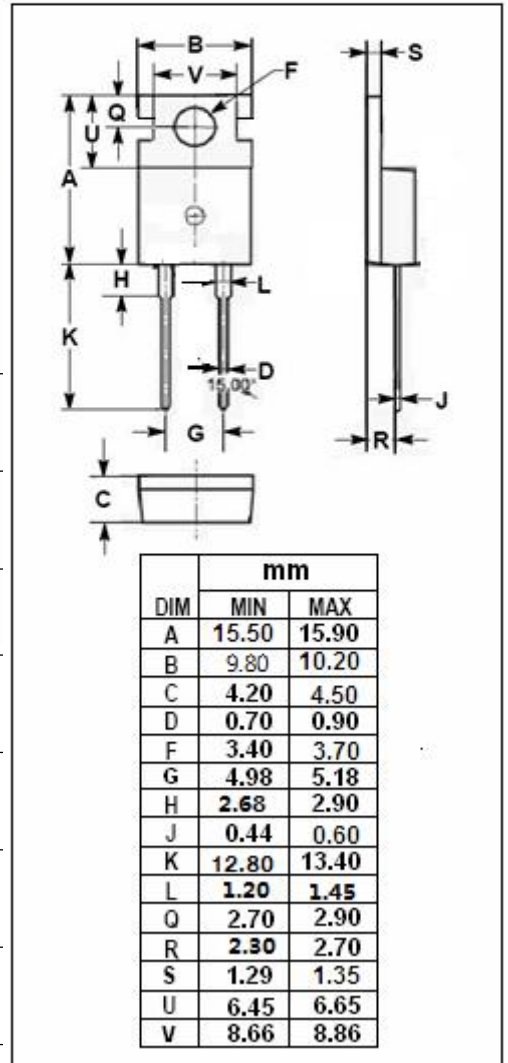
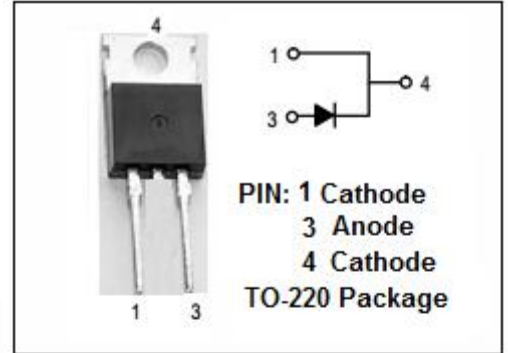
### APPLICATIONS

- For use in low voltage ,high frequency inverters, free wheeling and polarity protection applications.

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### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>R</sub> RM V <sub>R</sub> RMS V <sub>R</sub>	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	60	V
V <sub>R</sub> (RMS)	RMS Reverse Voltage	42	V
I <sub>F</sub> (AV)	Average Rectified Forward Current	10	A
I <sub>FSM</sub>	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	250	A
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C



**Schottky Barrier Rectifier****SBL1060****THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.5	$^{\circ}C/W$

**ELECTRICAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
$V_F$	Maximum Instantaneous Forward Voltage	$I_F=10A ; T_c= 25^{\circ}C$	0.75	V
$I_R$	Maximum Instantaneous Reverse Current	$V_R= V_{RWM}; T_c= 25^{\circ}C$	1.0	mA
		$V_R= V_{RWM}; T_c= 100^{\circ}C$	50	mA

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